

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (new) A rectifying charge storage device, comprising:
a rectifier structure fabricated with a common conductor forming a side of the rectifier structure; and
a capacitor structure fabricated as a single unitary structure with the rectifier structure such that the capacitor structure incorporates the common conductor of the rectifier structure as a side of the capacitor structure, the capacitor structure to receive the rectified current from the rectifier structure over the common conductor;
one of said rectifier structure and said capacitor structure including a bi-stable state element responsive to an input signal for changing from a first definable state to a second definable state for altering the electrical characteristics of the device.
2. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element is responsive to said input signal for reversibly changing between said first and second definable states.
3. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element is responsive to said input signal for irreversibly changing between said first and second definable states.
4. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element is incorporated into said rectifier structure.
5. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element is incorporated into said capacitor structure.

6. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element comprises a switching diode.

7. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element comprises a break diode.

8. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element comprises a switching capacitor.

9. (new) The rectifying charge storage device of claim 1, wherein said bi-stable state element comprises a break capacitor.

10. (new) The rectifying charge storage device of claim 1, wherein said first definable state comprises an open circuit condition, and said second definable state comprises a closed circuit condition.

11. (new) The rectifying charge storage device of claim 1, wherein said first definable state comprises a closed circuit condition, and said second definable state comprises an open circuit condition.

12. (new) The rectifying charge storage device of claim 1, wherein said first definable state comprises a more-conductive condition, and said second definable state comprises a less-conductive condition.

13. (new) The rectifying charge storage device of claim 1, wherein said first definable state comprises a less-conductive condition, and said second definable state comprises a more conductive condition.

14. (new) A rectifying charge storage device, comprising:
a rectifier;
a common conductor connected to one side of said rectifier;
a capacitor incorporating said common conductor;

said rectifier, common conductor and capacitor comprising a unitary element; and

a bi-stable state element responsive to an input signal for changing from a first definable state to a second definable state for altering the electrical characteristics of the device.

15. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element is responsive to said input signal for reversibly changing between said first and second definable states.

16. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element is irreversible.

17. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element is incorporated into said rectifier structure.

18. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element is incorporated into said capacitor structure.

19. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element comprises a switching diode.

20. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element comprises a break diode.

21. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element comprises a switching capacitor.

22. (new) The rectifying charge storage device of claim 14, wherein said bi-stable state element comprises a break capacitor.

23. (new) The rectifying charge storage device of claim 14, wherein said first definable state comprises an open circuit condition, and said second definable state comprises a closed circuit condition.

24. (new) The rectifying charge storage device of claim 14, wherein said first definable state comprises a closed circuit condition, and said second definable state comprises an open circuit condition.

25. (new) The rectifying charge storage device of claim 14, wherein said first definable state comprises a conductive condition, and said second definable state comprises a non-conductive condition.

26. (new) The rectifying charge storage device of claim 14, wherein said first definable state comprises a non-conductive condition, and said second definable state comprises a conductive condition.